

TENTATIVE

Features and Applications

- Low ON-state resistance.
- Low Qg

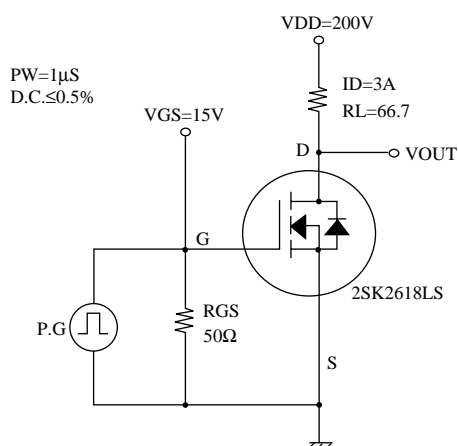
Absolute Maximum Ratings / Ta=25°C

| | | | unit |
|-----------------------------|--------------|-------------|------|
| Drain to Source Voltage | VDSS | 500 | V |
| Gate to Source Voltage | VGSS | ±30 | V |
| Drain Current (DC) | ID | 5 | A |
| Drain Current (Pulse) | IDP | 20 | A |
| Allowable power Dissipation | PD (Tc=25°C) | 30 | W |
| Channel Temperature | Tch | 150 | °C |
| Storage Temperature | Tstg | -55 to +150 | °C |

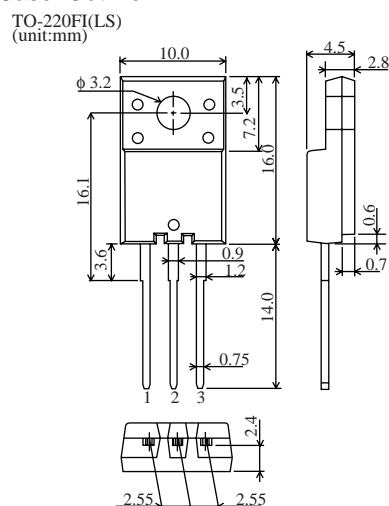
Electrical Characteristics / Ta=25°C

| | | | min | typ | max | unit |
|--|----------|----------------------------|-----|------|------|------|
| Drain to Source Breakdown Voltage | V(BR)DSS | ID=1mA , VGS=0 | 500 | | | V |
| Zero Gate Voltage Drain Current | IDSS | VDS=500V , VGS=0 | | | 1.0 | mA |
| Gate to Source Leakage Current | IGSS | VGS=±30V , VDS=0 | | | ±100 | nA |
| Cutoff Voltage | VGS(off) | VDS=10V , ID=1mA | 3.5 | | 5.5 | V |
| Forward Transfer Admittance | yfs | VDS=10V , ID=3A | 1.5 | 3.0 | | S |
| Static Drain to Source on State Resistance | RDS(on) | ID=3A , VGS=15V | | 0.95 | 1.25 | Ω |
| Input Capacitance | Ciss | VDS=20V , f=1MHz | | 700 | | pF |
| Output Capacitance | Coss | VDS=20V , f=1MHz | | 250 | | pF |
| Reverse Transfer Capacitance | Crss | VDS=20V , f=1MHz | | 120 | | pF |
| Total Gate Charge | Qg | VDS=200V , ID=5A GS=10V | | 20 | | nC |
| Turn-ON Delay Time | td(on) | See Specified Test Circuit | | 20 | | ns |
| Rise Time | tr | | | 20 | | ns |
| Turn-off Delay Time | td(off) | | | 50 | | ns |
| Fall Time | tf | | | 25 | | ns |
| Diode Forward Voltage | VSD | IS=5A , VGS=0 | | | 1.2 | V |

Switching Time Test Circuit



Case Outline



Specifications and information herein are subject to change without notice.

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